

# TLP520, TLP520-2, TLP520-4

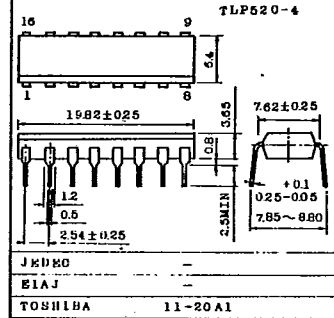
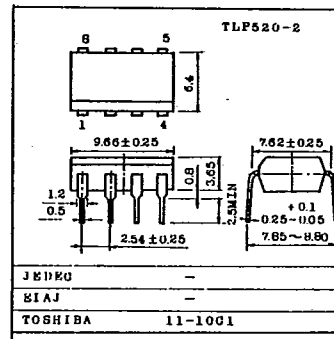
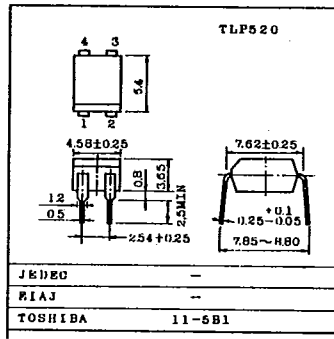
## GaAs IRED & PHOTO-TRANSISTOR

### AC/DC-INPUT MODULES PROGRAMMABLE CONTROLLERS

The TOSHIBA TLP520, -2 and -4 consist of two gallium arsenide infrared emitting diodes connected in inverse parallel and coupled with a silicon photo-transistor in a dual in-line package.  
The TLP520-2 offers two isolated channels in a single DIP package, while the TLP520-4 provides four isolated channels per package.

- AC or Polarity Insensitive Inputs
- Built-in Reverse Polarity Input Protection
- Isolation Voltage ..... 2500V<sub>rms</sub> Min.
- Current Transfer Ratio ..... 50% Min.
- BV<sub>CEO</sub> : 55V Min.
- UL Recognized : File No. E67349

Unit in mm



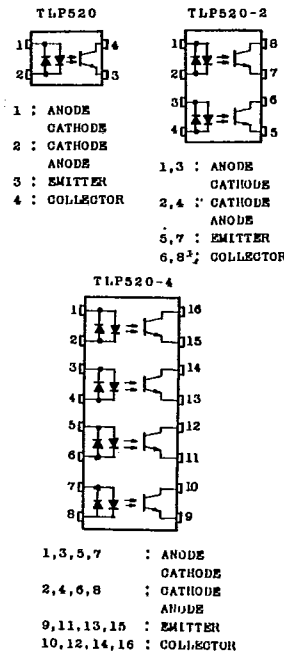
### MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING		UNIT	
		TLP520	TLP520-2, TLP520-4		
LED	Forward Current	IF(RMS)	60	50	mA
	Forward Current Derating	ΔIF/°C	-0.7 (Ta≥39°C)	-0.5 (Ta≥25°C)	mA/°C
	Pulse Forward Current	IFP	1 (100μs pulse, 100 pps)		A
DETECTOR	Collector-Emitter Voltage	V <sub>CEO</sub>	55		V
	Emitter-Collector Voltage	V <sub>ECO</sub>	7		V
	Collector Current	I <sub>C</sub>	50		mA
	Collector Power Dissipation (1 Circuit)	P <sub>C</sub>	150	100	mW
	Collector Power Dissipation Derating (1 Circuit) (Ta≥25°C)	ΔP <sub>C</sub> /°C	-1.5	-1.0	mW/°C
	Operating Temperature Range	T <sub>opr</sub>	-55 ~ 100		°C
	Storage Temperature Range	T <sub>stg</sub>	-55 ~ 150		°C
Total Power Dissipation	P <sub>T</sub>	250	150	mW	
Total Power Dissipation Derating (Ta≥25°C)	ΔP <sub>T</sub> /°C	-2.5	-1.5	mW/°C	
Isolation Voltage	B <sub>V</sub>	2500 (AC, 1 min., RH≤60%)		V <sub>rms</sub>	

### RECOMMENDED OPERATING CONDITIONS

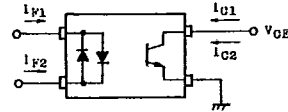
CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Supply Voltage	V <sub>CC</sub>	-	5	24	V
Forward Current	I <sub>F</sub>	-	-	20	mA
Operating Temperature Range	T <sub>opr</sub>	-25	-	85	°C

### PIN CONFIGURATIONS (TOP VIEW)



ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
LED	Forward Voltage	V <sub>F</sub>	I <sub>F</sub> =10mA	1.0	1.15	1.3	V
	Forward Current	I <sub>F</sub>	V <sub>F</sub> =1.7V	-	2.5	20	mA
	Capacitance	C <sub>T</sub>	V=0, f=1MHz	-	60	-	pF
DETECTOR	Collector-Emitter Breakdown Voltage	V(BR)CEO	I <sub>C</sub> =0.5mA	55	-	-	V
	Emitter-Collector Breakdown Voltage	V(BR)ECO	I <sub>E</sub> =0.1mA	7	-	-	V
	Collector Dark Current	I <sub>CEO</sub>	V <sub>CE</sub> =24V	-	10	100	nA
			V <sub>CE</sub> =24V, Ta=85°C	-	2	50	μA
	Capacitance Collector to Emitter	C <sub>CE</sub>	V <sub>CE</sub> =0, f=1MHz	-	10	-	pF
COUPLED	Current Transfer Ratio (Note 1)	I <sub>C</sub> /I <sub>F</sub>	I <sub>F</sub> =5mA, V <sub>CE</sub> =5V I <sub>F</sub> =1mA, V <sub>CE</sub> =0.4V	50	200	600	%
	Off-State Collector Current	I <sub>C(OFF)</sub>	V <sub>F</sub> =0.7V, V <sub>CE</sub> =24V	-	1	10	μA
	Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>F</sub> =8mA, I <sub>C</sub> =2.4mA	-	-	0.4	V
	Capacitance Input to Output	C <sub>S</sub>	V=0, f=1MHz	-	0.8	-	pF
	Isolation Resistance	R <sub>S</sub>	V=500V	5x10 <sup>10</sup>	10 <sup>14</sup>	-	Ω
	Rise and Fall Time	t <sub>r</sub> , t <sub>f</sub>	V <sub>CE</sub> =5V, R <sub>L</sub> =100Ω, I <sub>C</sub> =2mA	-	2.3	-	μs
CTR Symmetry (Note 2)	I <sub>C</sub> (Ratio)	I <sub>F</sub> =5mA, V <sub>CE</sub> =5V	0.33	-	3	-	



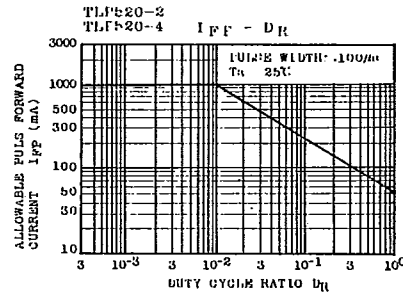
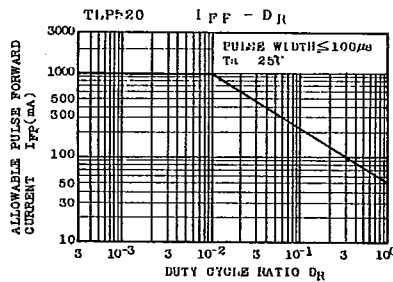
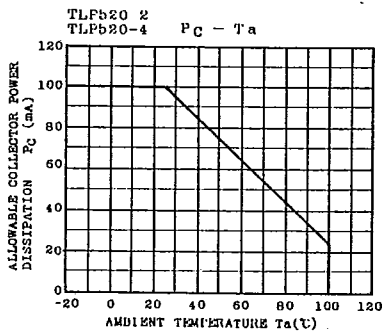
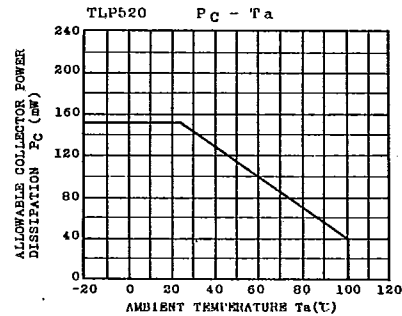
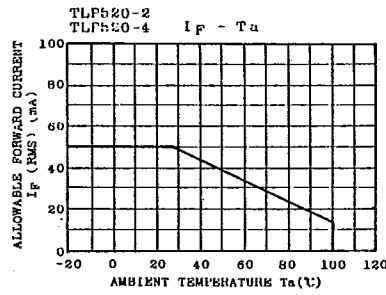
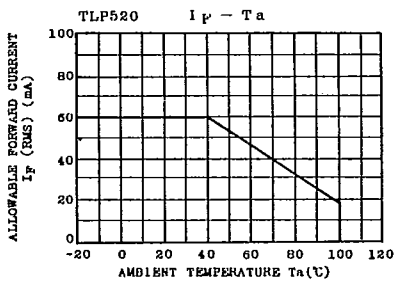
Note 1 : CTR rank

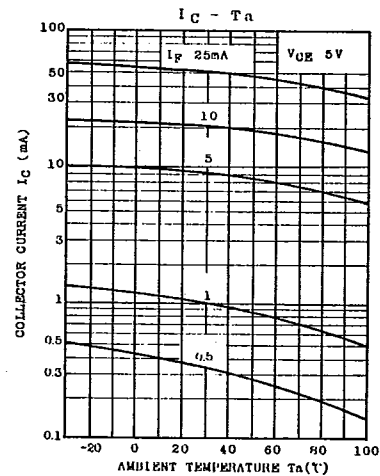
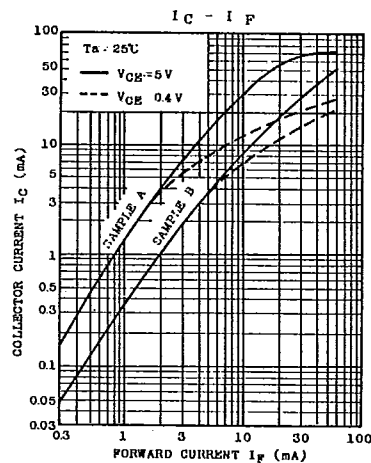
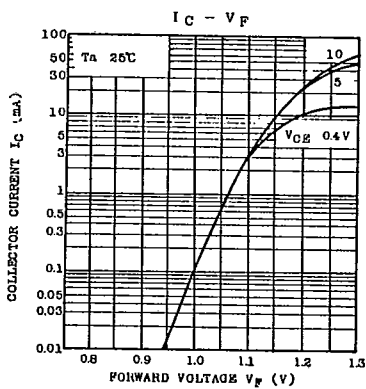
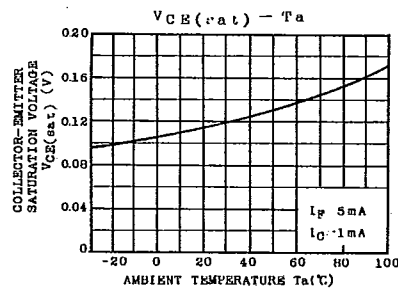
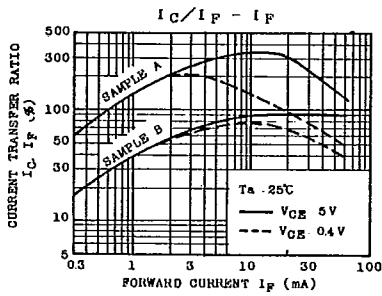
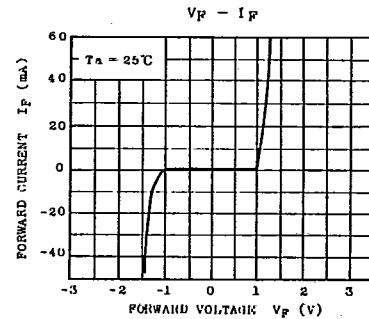
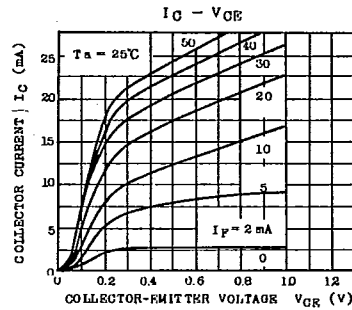
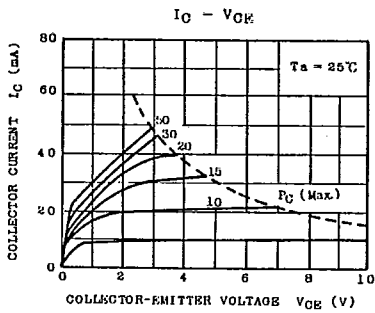
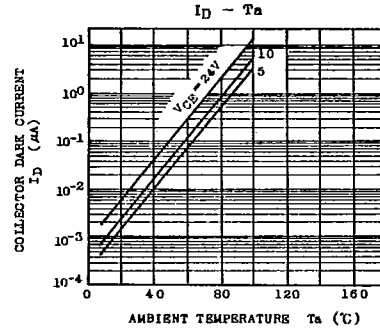
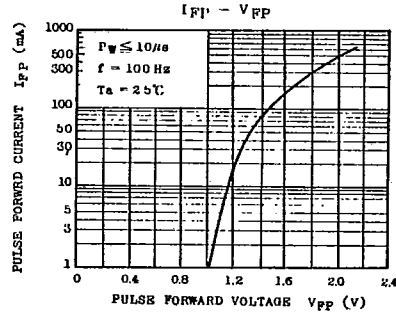
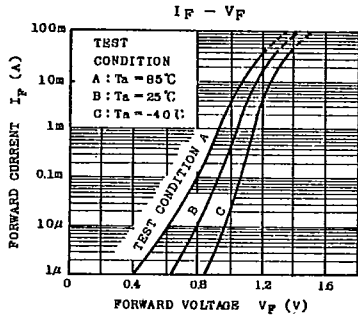
2 : I<sub>C</sub>(Ratio)

I<sub>C2</sub>(I<sub>F</sub>=5mA, V<sub>CE</sub>=5V)

I<sub>C1</sub>(I<sub>F</sub>=5mA, V<sub>CE</sub>=5V)

RANK NAME	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Rank GB	I <sub>F</sub> =5mA, V <sub>CE</sub> =5V	100	200	600	%
	I <sub>F</sub> =1mA, V <sub>CE</sub> =0.4V	50	100	-	%





$R_L$  - SWITCHING TIME

